

isc Silicon NPN Power Transistor

2SC3853

DESCRIPTION

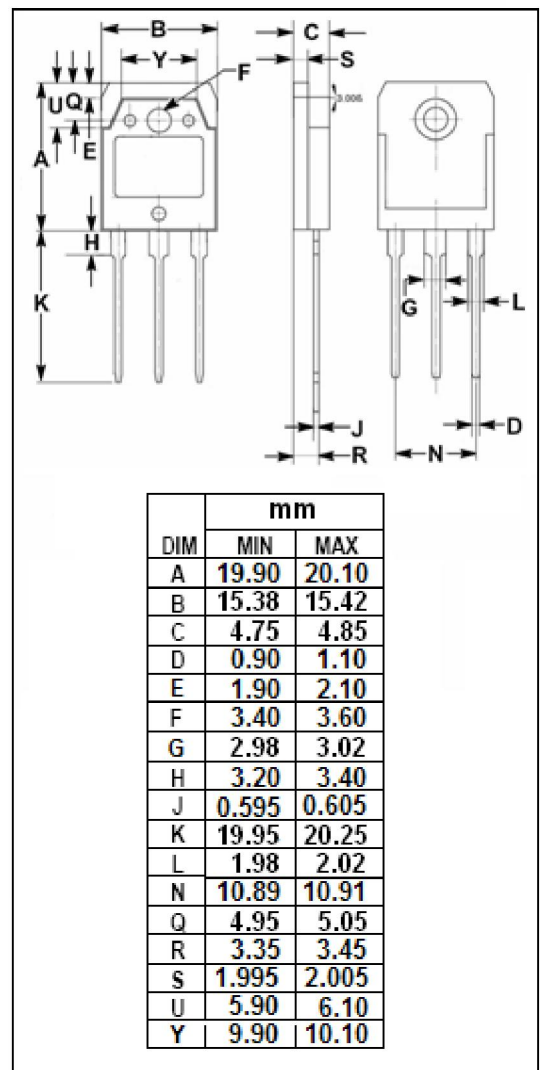
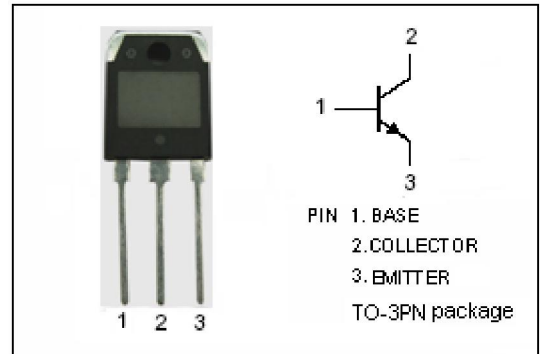
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- DC Current Gain-
: $h_{FE} = 50(\text{Min}) @ I_C = 2A$
- Complement to Type 2SA1489

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC3853****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA; I _B = 0	80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 0.2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			100	μ A
h _{FE}	DC Current Gain	I _C = 2A; V _{CE} = 4V	50			
f _T	Current-Gain—Bandwidth Product	I _E = -0.5A; V _{CE} = 12V		20		MHz

Switching Times

t _{on}	Turn-On Time	I _C = 3A; I _{B1} = -I _{B2} = 0.3A; V _{CC} = 30V; R _L = 10 Ω		0.5		μ s
t _{stg}	Storage Time			2.5		μ s
t _f	Fall Time			0.6		μ s